

**REMARKS / ARGUMENTS**

Claims 1-18 remain pending in this application. No claims have been canceled or added.

**Priority**

Applicants appreciate the Examiner's acknowledgment of the claim for priority and safe receipt of the priority document.

**35 U.S.C. §§102 and 103**

Claims 1-4, 10 and 17 stand rejected under 35 U.S.C. §102(b) as being anticipated by Zhang (U.S. Patent No. 5,814,529). Claim 6 stands rejected under 35 U.S.C. §103(a) as being unpatentable over Zhang in view of Tanabe et al (U.S. Patent No. 5,998,838). These rejections are traversed as follows.

The present invention, as recited in claim 1, is directed to an image display having a plurality of thin film transistors and a plurality of capacitors on a substrate. Each of the thin film transistors includes an island-shaped semiconductor layer, a first insulation film, and interlayer insulation film, and a source electrode and drain electrode which contact with a source region and a drain region via an opening formed in the interlayer insulation film. Each of the capacitors includes a storage

electrode, a second insulation film and an electrode formed on the second insulation film so as to be in contact therewith via an opening in the interlayer insulation film. The first insulation film is formed to cover the substrate and the second insulation film is patterned to be in contact with an upper surface and side surfaces of the storage electrode and an upper surface of the first insulation film.

Claim 1 has been amended to specify that a cross-section of an opening of the thin film transistor is constructed with layered films of a same insulation material (see, for example, specification, page 14, lines 8-11). Due to this point, a contact through hole can be made in a single etching process, thereby reducing the overall number of process steps.

On the other hand, in Zhang a silicon nitride film 209 is formed by dry etching (see column 4, lines 37-39). Thereafter, anisotropic dry etching is performed to a gate insulating film (silicon oxide) 204 and a silicon oxide film 208 (see column 4, lines 49-51). This is because film 209 and films 204 and 208 are formed from different materials. This increases the number of process steps involved and thus fails to realize the advantages realized by the present invention.

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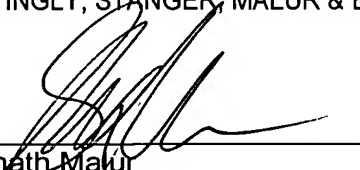
ASA-1050

**Conclusion**

In view of the foregoing, Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

Respectfully submitted,

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